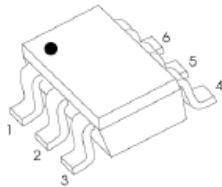
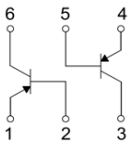


FEATURES

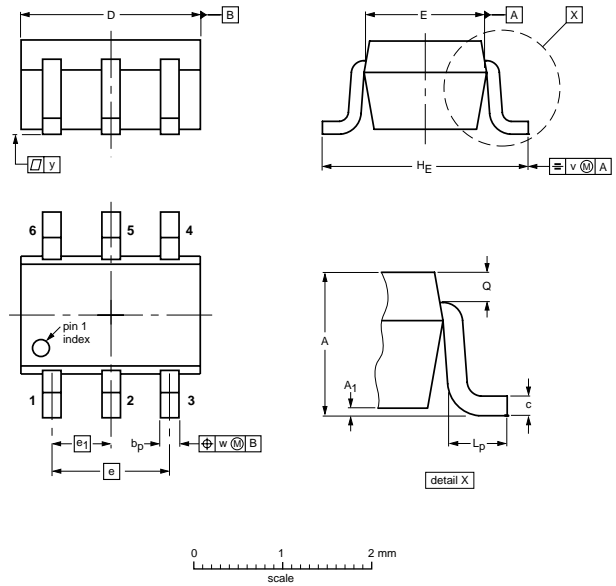
Epitaxial planar die construction
Ideal for low power amplification and switching

MARKING:K3N



SOT-363

SOT-363



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	bp	c	D	E	e	e ₁	H _E	L _p	Q	v	w	y
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V _{CB0}	Collector-Base Voltage	-40	V
V _{CEO}	Collector-Emitter Voltage	-40	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-0.2	A
P _C	Collector Power Dissipation	0.2	W
R _{θJA}	Thermal Resistance. Junction to Ambient Air	625	°C/W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

MMDT3906DW

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-10\mu A, I_E=0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu A, I_C=0$	-5			V
Collector cut-off current	I_{CEX}	$V_{CE}=-30V, V_{EB(OFF)}=-3V$			-50	nA
Base cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$			-50	nA
DC current gain	$h_{FE(1)}$	$V_{CE}=-1V, I_C=-0.1mA$	60			
	$h_{FE(2)}$	$V_{CE}=-1V, I_C=-1mA$	80			
	$h_{FE(3)}$	$V_{CE}=-1V, I_C=-10mA$	100		300	
	$h_{FE(4)}$	$V_{CE}=-1V, I_C=-50mA$	60			
	$h_{FE(5)}$	$V_{CE}=-1V, I_C=-100mA$	30			
Collector-emitter saturation voltage	$V_{CE(sat)1}$	$I_C=-10mA, I_B=-1mA$			-0.25	V
	$V_{CE(sat)2}$	$I_C=-50mA, I_B=-5mA$			-0.4	V
Base-emitter saturation voltage	$V_{BE(sat)1}$	$I_C=-10mA, I_B=-1mA$	-0.65		-0.85	V
	$V_{BE(sat)2}$	$I_C=-50mA, I_B=-5mA$			-0.95	V
Transition frequency	f_T	$V_{CE}=-20V, I_C=-10mA, f=100MHz$	250			MHz
Collector output capacitance	C_{ob}	$V_{CB}=-5V, I_E=0, f=1MHz$			4.5	pF
Noise figure	NF	$V_{CE}=-5V, I_C=-0.1mA, f=1KHz, R_g=1K\Omega$			4	dB
Delay time	t_d	$V_{CC}=-3V, V_{BE}=0.5V$			35	nS
Rise time	t_r	$I_C=-10mA, I_{B1}=-I_{B2}=-1mA$			35	nS
Storage time	t_s	$V_{CC}=-3V, I_C=-10mA$			225	nS
Fall time	t_f	$I_{B1}=-I_{B2}=-1mA$			75	nS

RATING AND CHARACTERISTIC CURVES (MMDT3906DW)

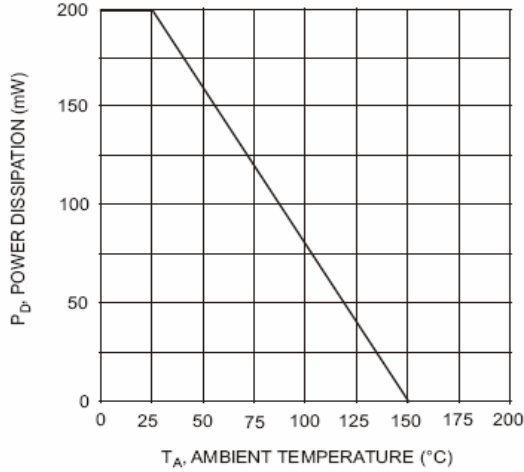


Fig. 1, Max Power Dissipation vs Ambient Temperature

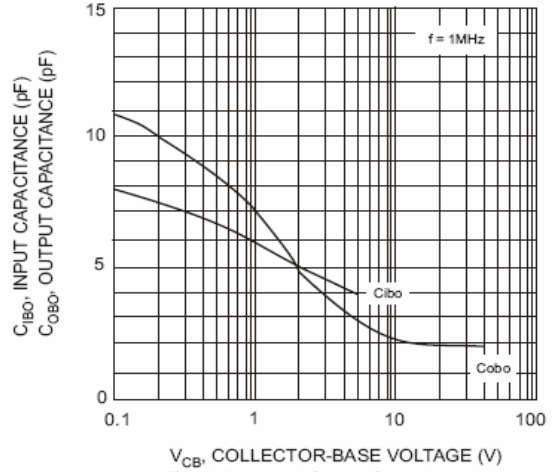


Fig. 2, Input and Output Capacitance vs. Collector-Base Voltage

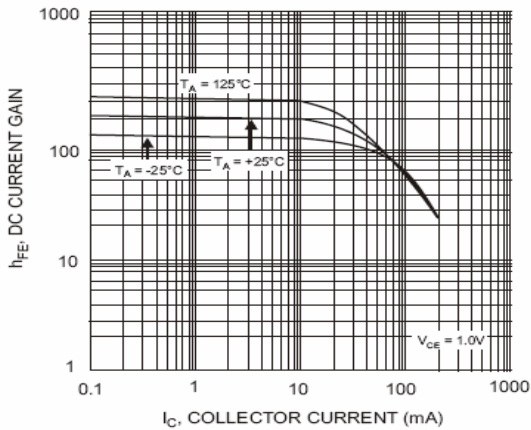


Fig. 3, Typical DC Current Gain vs Collector Current

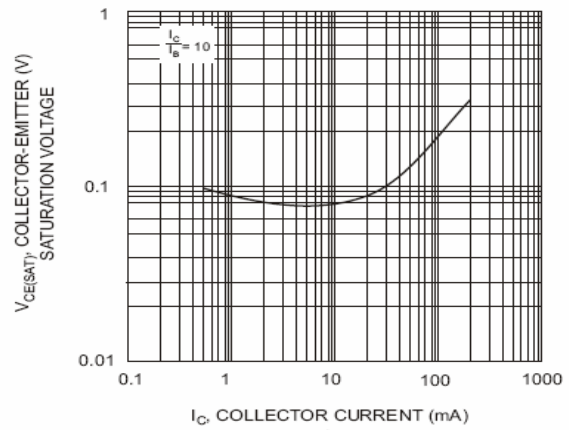


Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current

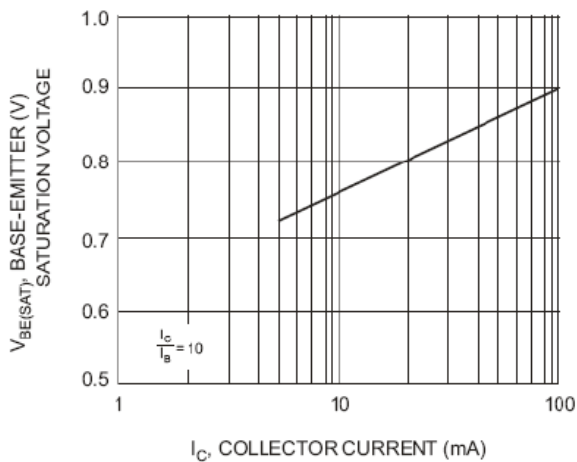


Fig. 5, Typical Base-Emitter Saturation Voltage vs. Collector Current

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